

SILICON PNP EPITAXIAL TYPE

BC556~558

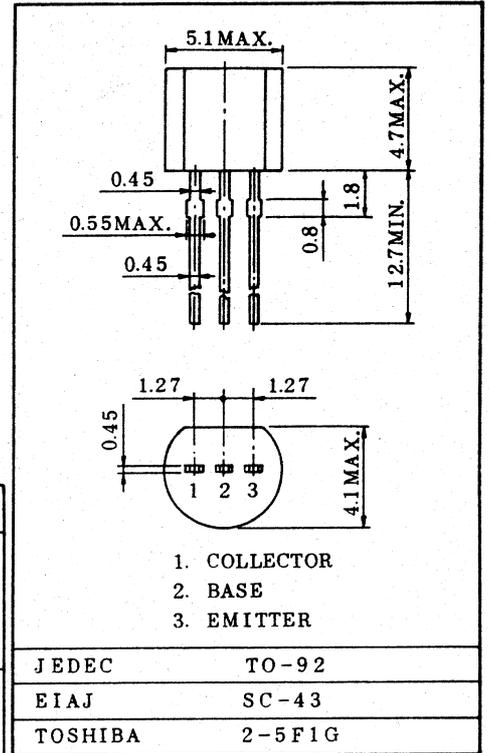
PRIMARILY INTENDED FOR USE DRIVER STAGE OF AUDIO AMPLIFIERS.

- . High V_{CEO} : -65V (TBC556)
 -45V (TBC557)
 -30V (TBC558)
- . Low Noise

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Breakdown Voltage	TBC556	$V_{(BR)CBO}$	-80	V
	TBC557		-50	
	TBC558		-30	
Collector-Emitter Breakdown Voltage	TBC556	$V_{(BR)CEO}$	-65	V
	TBC557		-45	
	TBC558		-30	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	-5	V
Collector Current	DC	I_C	-100	mA
	Peak	I_{CP}	-200	
Base Current (Peak)		I_{BP}	-200	mA
Collector Power Dissipation		P_C	500	mW
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-65~150	$^\circ\text{C}$

Unit in mm



Weight : 0.21g

